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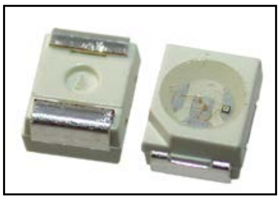
GUVB-S11SD



TECHNICAL DATA

UV-B Sensor

Features

- Aluminium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- Good Visible Blindness
- High Responsivity & Low Dark Current

Applications

- UV Index Monitoring
- UV-B Lamp Monitoring

Absolute Maximum Ratings

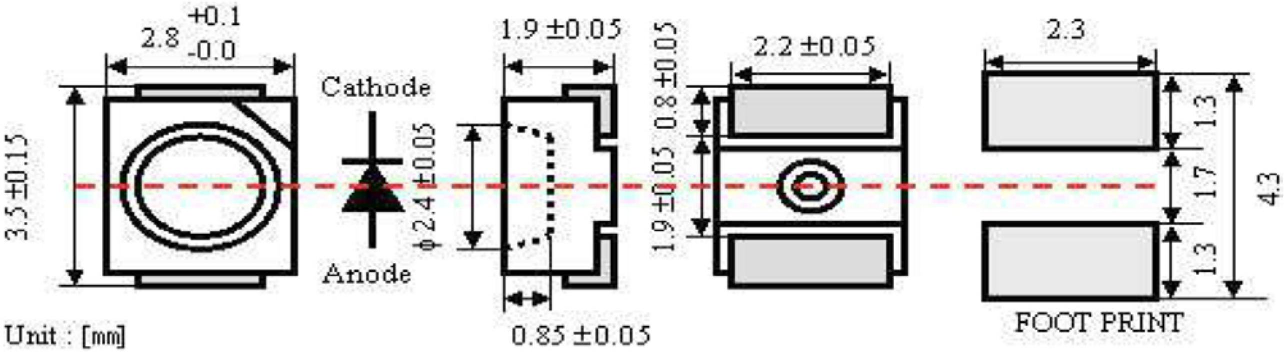
Item	Symbol	Value	Unit
Forward Current	I_F	1	mA
Reverse Voltage	V_R	3	V
Operating Temperature	T_{op}	-30 … +85	°C
Storage Temperature	T_{st}	-40 … +90	°C
Soldering Temperature *	T_{sol}	260	°C

* must be completed within 10 seconds

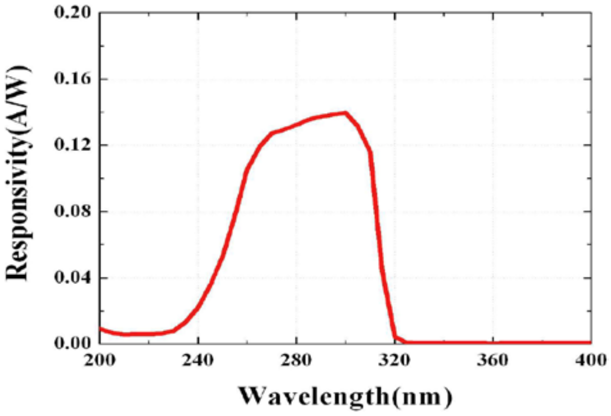
Characteristics (25°C)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Dark Current	I_D	V_R = 0.1 V	-	-	1	nA
Photo Current	I_{PD}	UVB Lamp, 1 mW/cm²	-	69	-	nA
		1 UVI	-	1.4	-	nA
Temperature Coefficient	I_{TC}	UVB Lamp	-	0.1	-	% / °C
Responsivity	R	λ = 300 nm, V_R = 0 V	-	0.14	-	A/W
Spectral Detection Range	λ	10% of R	235	-	320	nm

Package Dimension



Responsivity Curve



Photocurrent along UV Power